



# ACTT8B-800C0T

## AC Thyristor Triac power switch

25 March 2014

Product data sheet

### 1. General description

AC Thyristor Triac power switch in a SOT404 (D2PAK) surface mountable plastic package with self-protective clamping capabilities against low and high energy transients. This "series C0T" triac will commutate the full RMS current at the maximum rated junction temperature ( $T_{j(max)} = 150\text{ °C}$ ) without the aid of a snubber. It is used in applications where "high junction operating temperature capability" is required.

### 2. Features and benefits

- Clamping structure ensuring safe high over-voltage withstand capability
- High junction operating temperature capability
- High minimum  $I_{GT}$  for guaranteed immunity to gate noise
- Full cycle AC conduction
- Over-voltage withstand capability to IEC 61000-4-5
- Pin compatible with standard triacs
- Planar passivated for voltage ruggedness and reliability
- Protective self turn-on capability for high energy transients
- Safe clamping capability for low energy over-voltage transients
- Less sensitive gate for high noise immunity
- Surface mountable package
- Triggering in three quadrants only
- Very high immunity to false turn-on by  $dV/dt$

### 3. Applications

- AC fan, pump and compressor controls
- Highly inductive, resistive and safety loads
- Large and small appliances (White Goods)
- Reversing induction motor controls
- Applications subject to high temperature

### 4. Quick reference data

Table 1. Quick reference data

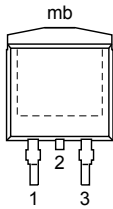
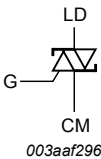
| Symbol    | Parameter                            | Conditions  | Min | Typ | Max | Unit |
|-----------|--------------------------------------|---|-----|-----|-----|------|
| $V_{DRM}$ | repetitive peak off-state voltage    |   | -   | -   | 800 | V    |
| $I_{TSM}$ | non-repetitive peak on-state current | full sine wave; $T_{j(init)} = 25\text{ °C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | -   | 80  | A    |



| Symbol                         | Parameter                             | Conditions   | Min | Typ | Max | Unit       |
|--------------------------------|---------------------------------------|--|-----|-----|-----|------------|
| $T_j$                          | junction temperature                  |  | -   | -   | 150 | °C         |
| $I_{T(RMS)}$                   | RMS on-state current                  | full sine wave; $T_{mb} \leq 130$ °C; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>               | -   | -   | 8   | A          |
| $V_{PP}$                       | peak pulse voltage                    | $T_j = 25$ °C; non-repetitive, off-state; <a href="#">Fig. 6</a>   | -   | -   | 2   | kV         |
| <b>Static characteristics</b>  |                                       |  |     |     |     |            |
| $I_{GT}$                       | gate trigger current                  | $V_D = 12$ V; $I_T = 100$ mA; LD+ G+; $T_j = 25$ °C; <a href="#">Fig. 8</a>  | 5   | -   | 30  | mA         |
|                                |                                       | $V_D = 12$ V; $I_T = 100$ mA; LD+ G-; $T_j = 25$ °C; <a href="#">Fig. 8</a>  | 5   | -   | 30  | mA         |
|                                |                                       | $V_D = 12$ V; $I_T = 100$ mA; LD- G-; $T_j = 25$ °C; <a href="#">Fig. 8</a>  | 5   | -   | 30  | mA         |
| $V_{CL}$                       | clamping voltage                      | $I_{CL} = 0.1$ mA; $t_p = 1$ ms; $T_j = 25$ °C   | 850 | -   | -   | V          |
| <b>Dynamic characteristics</b> |                                       |  |     |     |     |            |
| $dV_D/dt$                      | rate of rise of off-state voltage     | $V_{DM} = 536$ V; $T_j = 150$ °C; ( $V_{DM} = 67\%$ of $V_{DRM}$ ); exponential waveform; gate open circuit                  | 600 | -   | -   | V/ $\mu$ s |
| $dI_{com}/dt$                  | rate of change of commutating current | $V_D = 400$ V; $T_j = 150$ °C; $I_{T(RMS)} = 8$ A; $dV_{com}/dt = 20$ V/ $\mu$ s; (snubberless condition); gate open circuit | 3   | -   | -   | A/ms       |

## 5. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description         | Simplified outline   | Graphic symbol   |
|-----|--------|---------------------|--|--|
| 1   | CM     | common              |  <p style="text-align: center;"><b>D2PAK (SOT404)</b></p> |  <p style="text-align: center;">003aaf296</p> |
| 2   | LD     | load                |  |  |
| 3   | G      | gate                |  |  |
| mb  | LD     | mounting base; load |  |  |

## 6. Ordering information

Table 3. Ordering information

| Type number   | Package |  |         |
|---------------|---------|--|---------|
|               | Name    | Description  | Version |
| ACTT8B-800C0T | D2PAK   | plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) | SOT404  |

## 7. Marking

Table 4. Marking codes

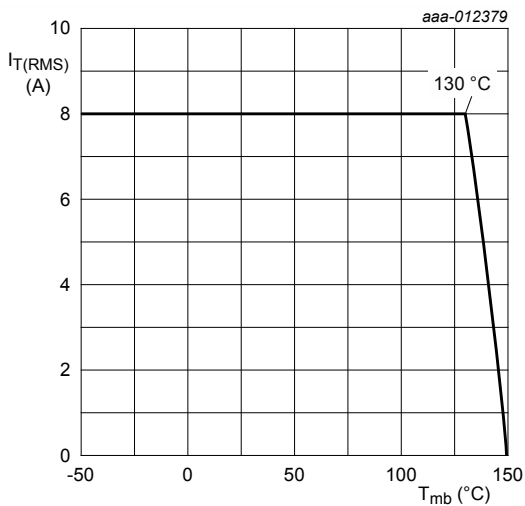
| Type number   | Marking code  |
|---------------|---------------|
| ACTT8B-800C0T | ACTT8B-800C0T |

## 8. Limiting values

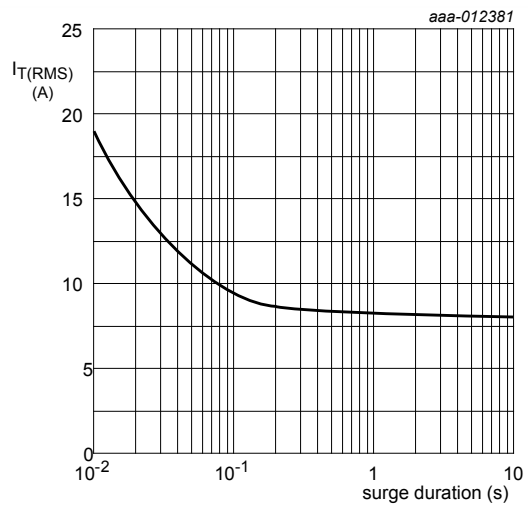
**Table 5. Limiting values**

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol       | Parameter                            | Conditions   | Min | Max | Unit                   |
|--------------|--------------------------------------|--|-----|-----|------------------------|
| $V_{DRM}$    | repetitive peak off-state voltage    |  | -   | 800 | V                      |
| $I_{T(RMS)}$ | RMS on-state current                 | full sine wave; $T_{mb} \leq 130\text{ }^\circ\text{C}$ ; <a href="#">Fig. 1</a> ; <a href="#">Fig. 2</a> ; <a href="#">Fig. 3</a>       | -   | 8   | A                      |
| $I_{TSM}$    | non-repetitive peak on-state current | full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 20\text{ ms}$ ; <a href="#">Fig. 4</a> ; <a href="#">Fig. 5</a> | -   | 80  | A                      |
|              |                                      | full sine wave; $T_{j(\text{init})} = 25\text{ }^\circ\text{C}$ ; $t_p = 16.7\text{ ms}$   | -   | 88  | A                      |
| $I^2t$       | $I^2t$ for fusing                    | $t_p = 10\text{ ms}$ ; sine-wave pulse   | -   | 32  | $\text{A}^2\text{s}$   |
| $di_T/dt$    | rate of rise of on-state current     | $I_T = 12\text{ A}$ ; $I_G = 0.2\text{ A}$ ; $di_G/dt = 0.2\text{ A}/\mu\text{s}$  | -   | 100 | $\text{A}/\mu\text{s}$ |
| $I_{GM}$     | peak gate current                    | $t = 20\text{ }\mu\text{s}$  | -   | 2   | A                      |
| $P_{GM}$     | peak gate power                      |  | -   | 5   | W                      |
| $P_{G(AV)}$  | average gate power                   | over any 20 ms period  | -   | 0.5 | W                      |
| $T_{stg}$    | storage temperature                  |  | -40 | 150 | $^\circ\text{C}$       |
| $T_j$        | junction temperature                 |  | -   | 150 | $^\circ\text{C}$       |
| $V_{PP}$     | peak pulse voltage                   | $T_j = 25\text{ }^\circ\text{C}$ ; non-repetitive, off-state; <a href="#">Fig. 6</a>   | -   | 2   | kV                     |



**Fig. 1. RMS on-state current as a function of mounting base temperature; maximum values**



$f = 50\text{ Hz}$ ;  $T_{mb} = 130\text{ }^\circ\text{C}$

**Fig. 2. RMS on-state current as a function of surge duration; maximum values**

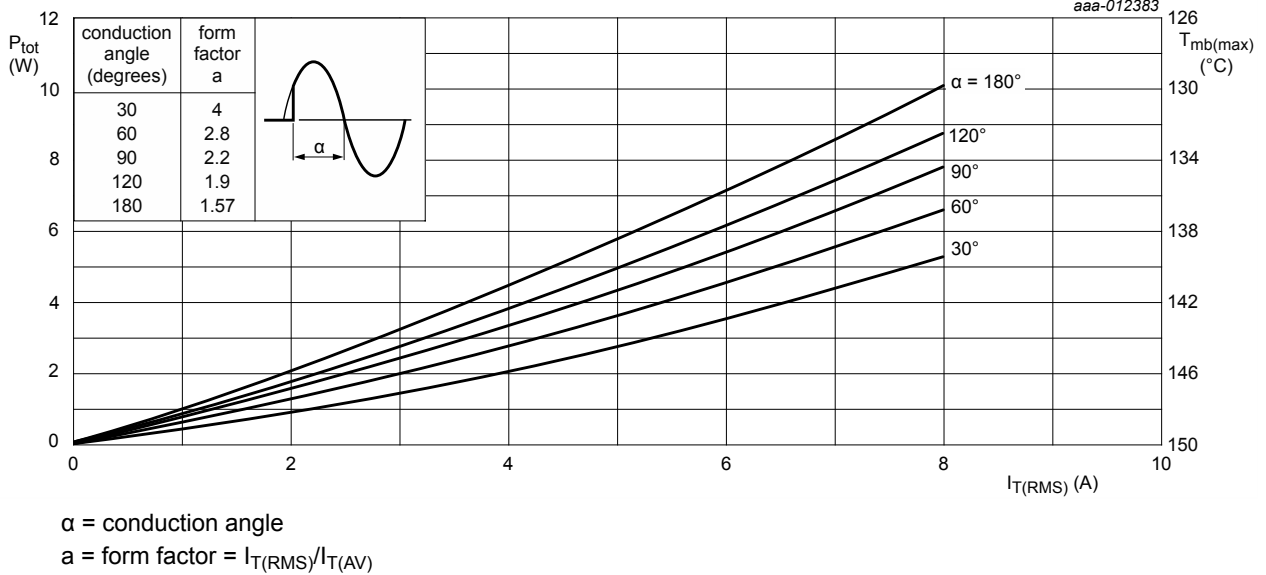


Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

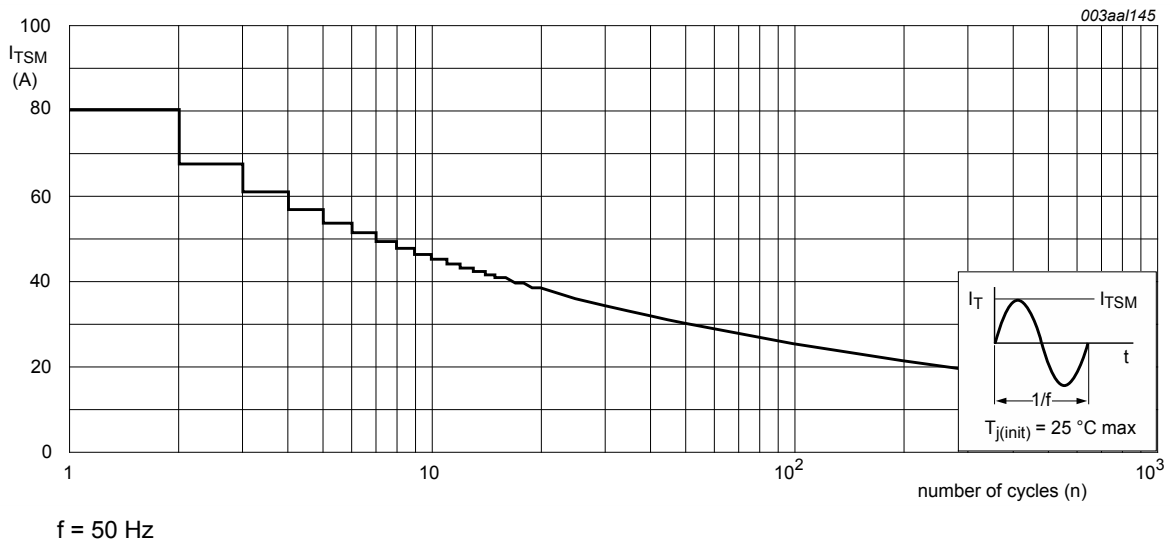


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values

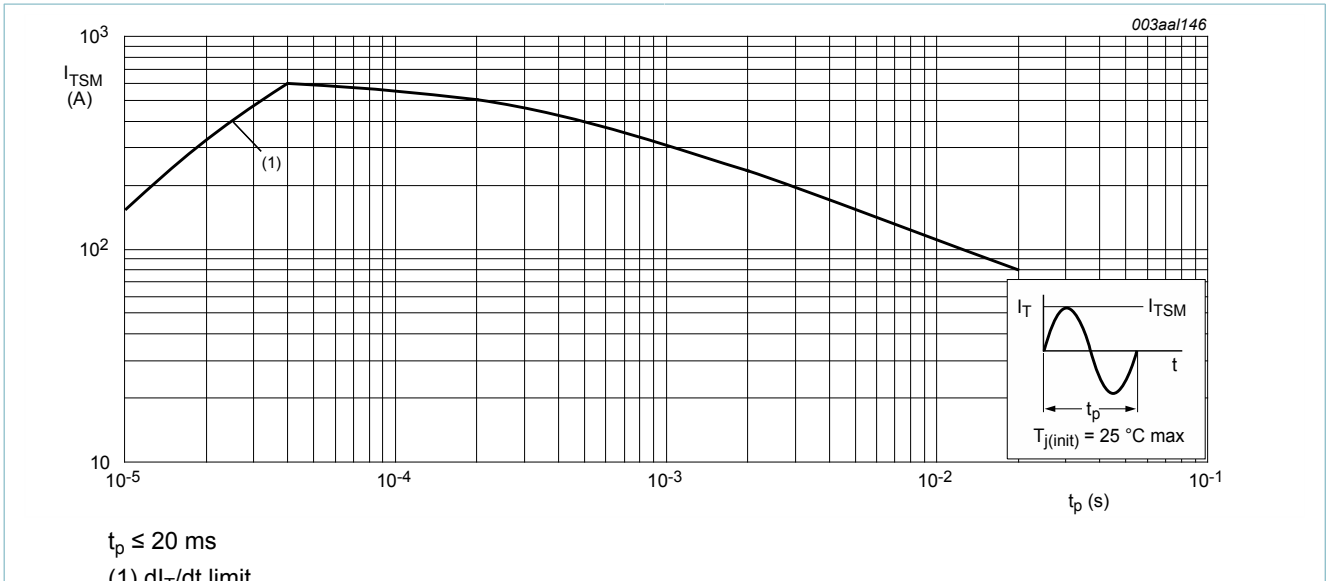


Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

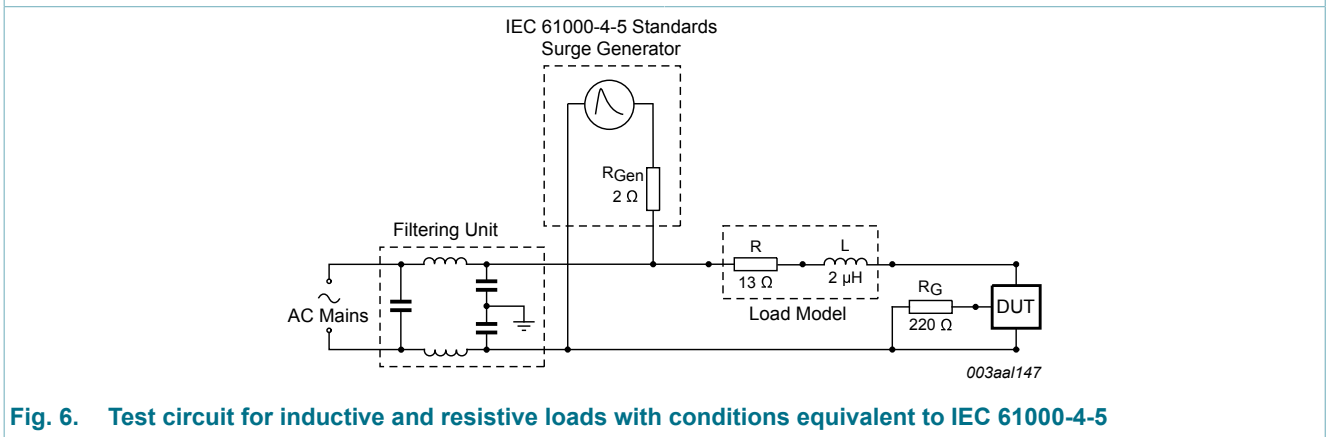
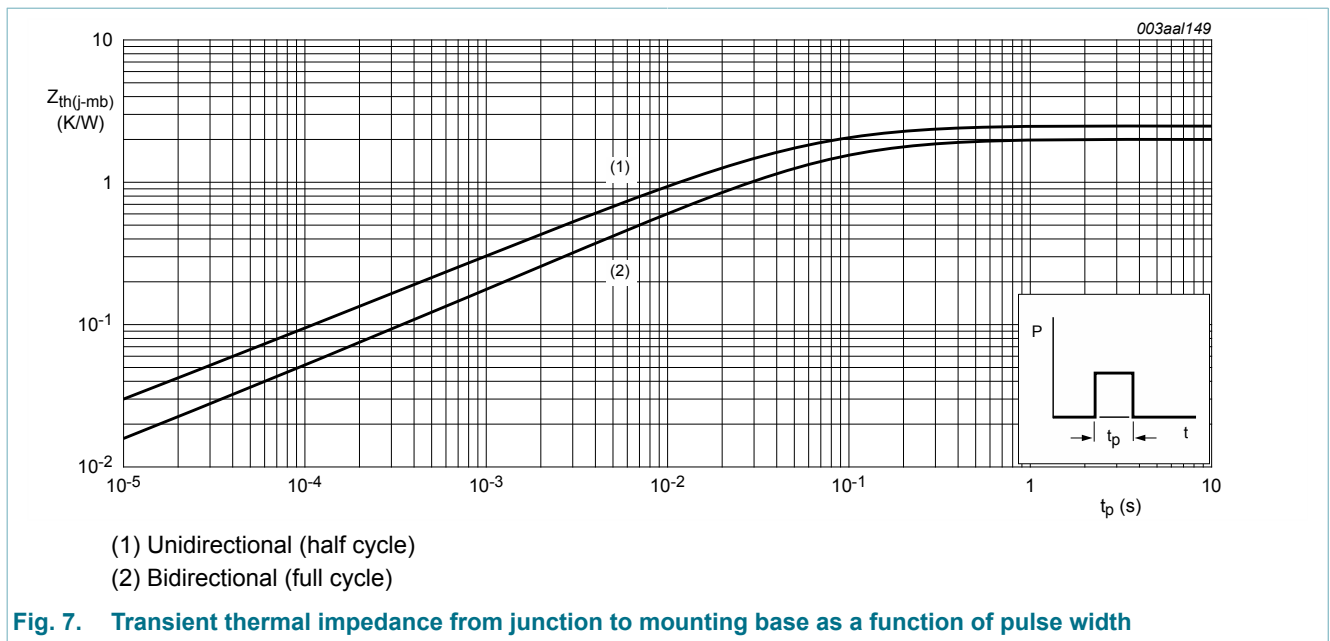


Fig. 6. Test circuit for inductive and resistive loads with conditions equivalent to IEC 61000-4-5

### 9. Thermal characteristics

Table 6. Thermal characteristics

| Symbol         | Parameter   | Conditions                                       | Min | Typ | Max | Unit |
|----------------|---|--|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | full cycle; <a href="#">Fig. 7</a>               | -   | -   | 2   | K/W  |
|                |   | half cycle; <a href="#">Fig. 7</a>               | -   | -   | 2.4 | K/W  |
| $R_{th(j-a)}$  | thermal resistance from junction to ambient       | in free air; printed circuit board (FR4) mounted | -   | 55  | -   | K/W  |

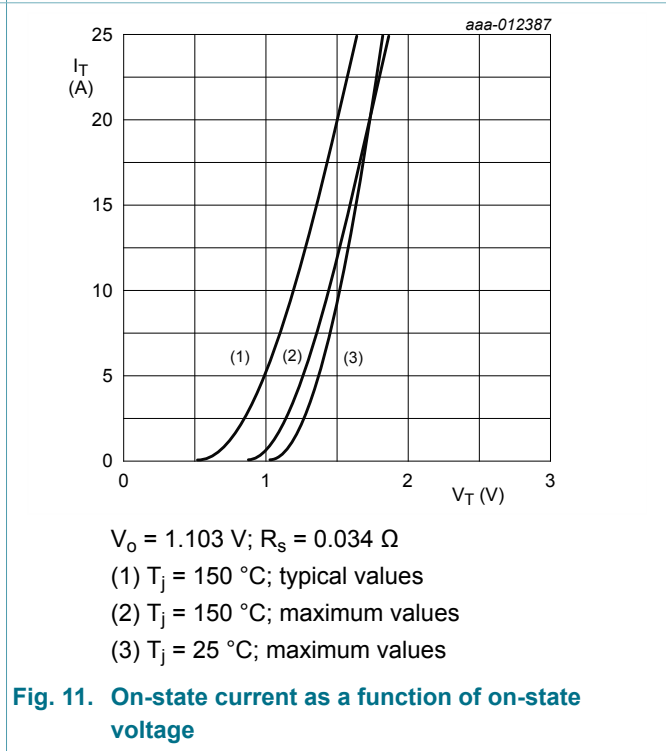
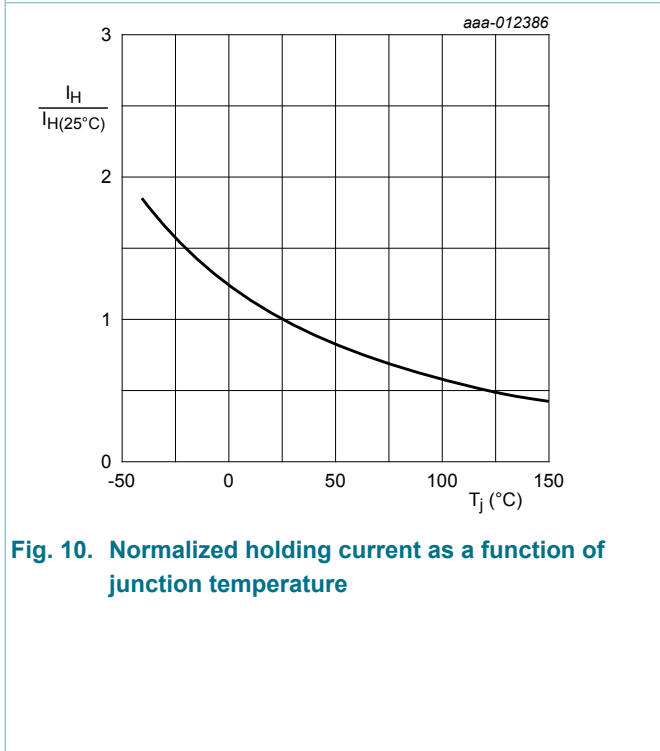
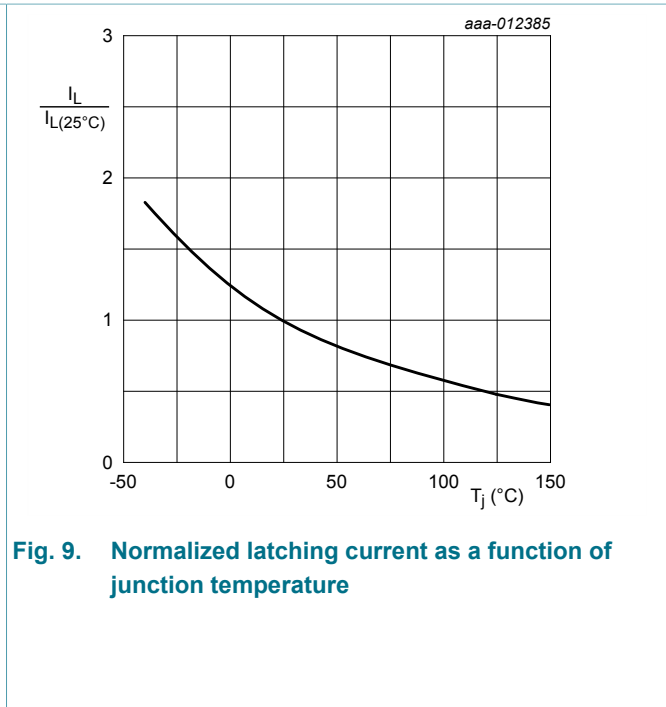
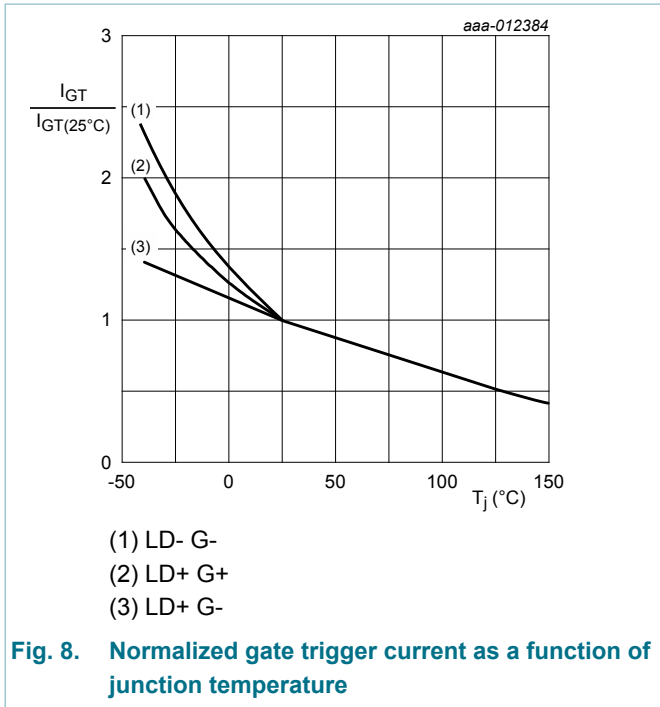


## 10. Characteristics

Table 7. Characteristics

| Symbol                         | Parameter                             | Conditions  | Min | Typ  | Max | Unit |
|--------------------------------|---------------------------------------|---|-----|------|-----|------|
| <b>Static characteristics</b>  |                                       |   |     |      |     |      |
| I <sub>GT</sub>                | gate trigger current                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>  | 5   | -    | 30  | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>  | 5   | -    | 30  | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 8</a>  | 5   | -    | 30  | mA   |
| I <sub>L</sub>                 | latching current                      | V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD+ G+; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>  | -   | -    | 50  | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD+ G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>  | -   | -    | 70  | mA   |
|                                |                                       | V <sub>D</sub> = 12 V; I <sub>G</sub> = 100 mA; LD- G-; T <sub>j</sub> = 25 °C; <a href="#">Fig. 9</a>  | -   | -    | 50  | mA   |
| I <sub>H</sub>                 | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <a href="#">Fig. 10</a>  | -   | -    | 35  | mA   |
| V <sub>T</sub>                 | on-state voltage                      | I <sub>T</sub> = 10 A; T <sub>j</sub> = 25 °C; <a href="#">Fig. 11</a>  | -   | 1.3  | 1.5 | V    |
| V <sub>GT</sub>                | gate trigger voltage                  | V <sub>D</sub> = 12 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 25 °C; <a href="#">Fig. 12</a>   | -   | 0.8  | 1   | V    |
|                                |                                       | V <sub>D</sub> = 400 V; I <sub>T</sub> = 100 mA; T <sub>j</sub> = 150 °C; <a href="#">Fig. 12</a>   | 0.2 | 0.45 | -   | V    |
| I <sub>D</sub>                 | off-state current                     | V <sub>D</sub> = 800 V; T <sub>j</sub> = 25 °C  | -   | -    | 10  | µA   |
|                                |                                       | V <sub>D</sub> = 800 V; T <sub>j</sub> = 150 °C   | -   | -    | 2   | mA   |
| V <sub>CL</sub>                | clamping voltage                      | I <sub>CL</sub> = 0.1 mA; t <sub>p</sub> = 1 ms; T <sub>j</sub> = 25 °C   | 850 | -    | -   | V    |
| <b>Dynamic characteristics</b> |                                       |   |     |      |     |      |
| dV <sub>D</sub> /dt            | rate of rise of off-state voltage     | V <sub>DM</sub> = 536 V; T <sub>j</sub> = 150 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit                 | 600 | -    | -   | V/µs |
| di <sub>com</sub> /dt          | rate of change of commutating current | V <sub>D</sub> = 400 V; T <sub>j</sub> = 150 °C; I <sub>T(RMS)</sub> = 8 A; dV <sub>com</sub> /dt = 20 V/µs; (snubberless condition); gate open circuit | 3   | -    | -   | A/ms |





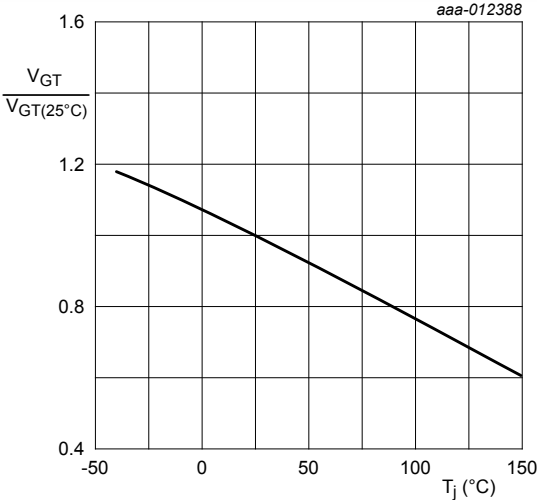
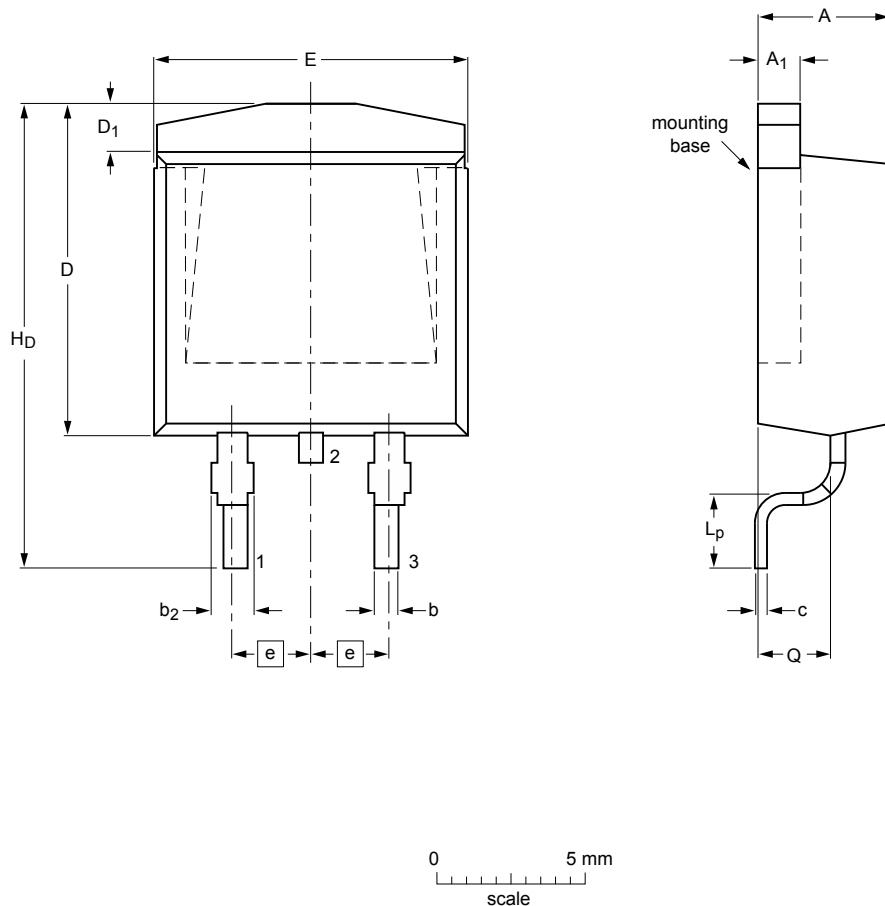


Fig. 12. Normalized gate trigger voltage as a function of junction temperature

11. Package outline

Plastic single-ended surface-mounted package (D2PAK); 3 leads (one lead cropped) SOT404



Dimensions (mm are the original dimensions)

| Unit | A   | A <sub>1</sub> | b    | b <sub>2</sub> | c    | D  | D <sub>1</sub> | E    | e    | H <sub>D</sub> | L <sub>p</sub> | Q   |
|------|-----|----------------|------|----------------|------|----|----------------|------|------|----------------|----------------|-----|
| max  | 4.5 | 1.40           | 0.85 | 1.45           | 0.64 | 11 | 1.6            | 10.3 |      | 15.8           | 2.9            | 2.6 |
| nom  |     |                |      |                |      |    |                |      | 2.54 |                |                |     |
| min  | 4.1 | 1.27           | 0.60 | 1.05           | 0.46 |    | 1.2            | 9.7  |      | 14.8           | 2.1            | 2.2 |

sot404\_po

| Outline version | References |       |       | European projection | Issue date             |
|-----------------|------------|-------|-------|---------------------|------------------------|
|                 | IEC        | JEDEC | JEITA |                     |                        |
| SOT404          |            |       |       |                     | -06-03-16-<br>13-02-25 |

Fig. 13. Package outline D2PAK (SOT404)

## 12. Soldering

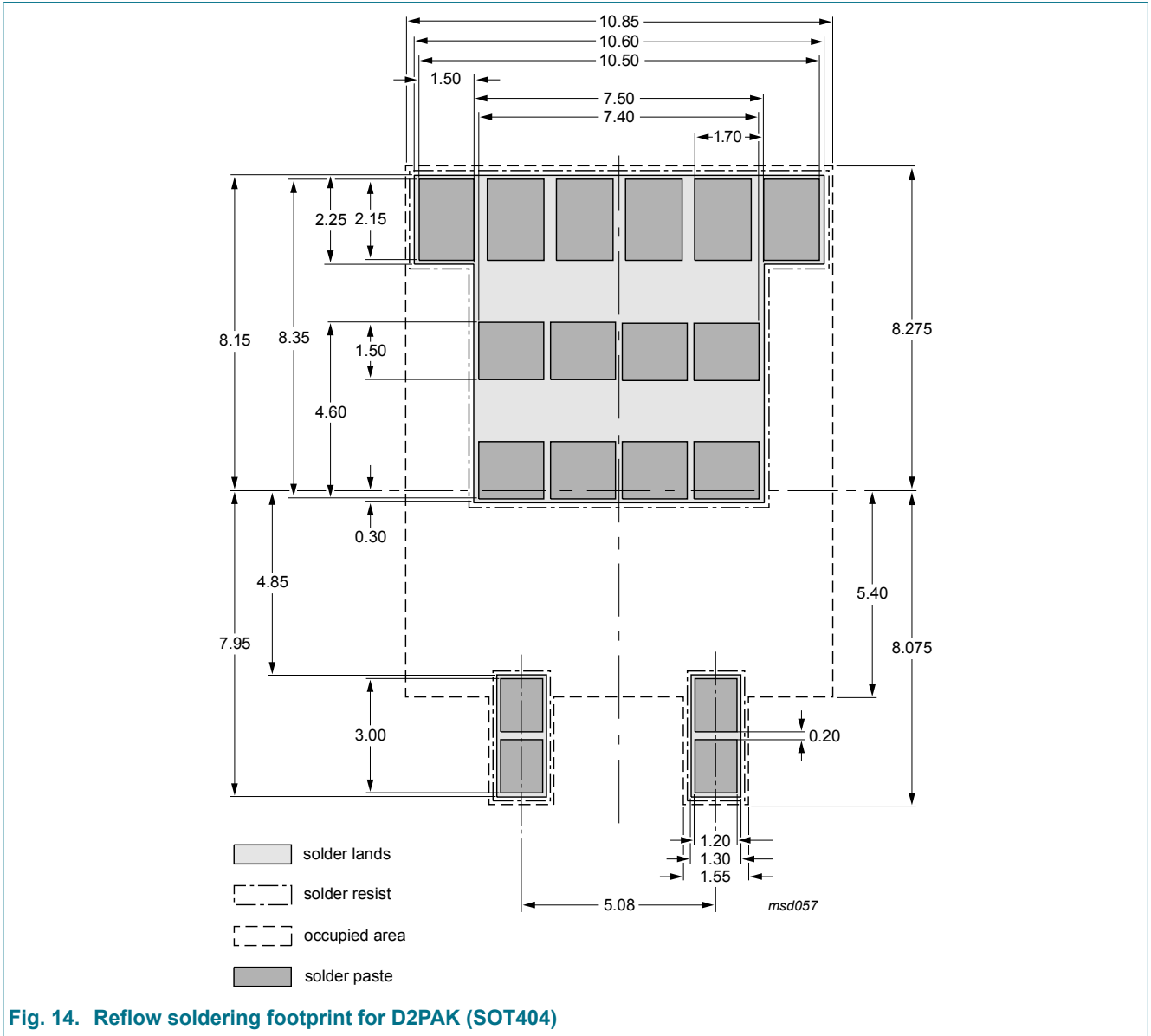


Fig. 14. Reflow soldering footprint for D2PAK (SOT404)

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|--------------------------------|--------------------|---|
| Objective [short] data sheet   | Development        | This document contains data from the objective specification for product development. |
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Компания «Океан Электроники» предлагает заключение долгосрочных отношений при поставках импортных электронных компонентов на взаимовыгодных условиях!

Наши преимущества:

- Поставка оригинальных импортных электронных компонентов напрямую с производств Америки, Европы и Азии, а так же с крупнейших складов мира;
- Широкая линейка поставок активных и пассивных импортных электронных компонентов (более 30 млн. наименований);
- Поставка сложных, дефицитных, либо снятых с производства позиций;
- Оперативные сроки поставки под заказ (от 5 рабочих дней);
- Экспресс доставка в любую точку России;
- Помощь Конструкторского Отдела и консультации квалифицированных инженеров;
- Техническая поддержка проекта, помощь в подборе аналогов, поставка прототипов;
- Поставка электронных компонентов под контролем ВП;
- Система менеджмента качества сертифицирована по Международному стандарту ISO 9001;
- При необходимости вся продукция военного и аэрокосмического назначения проходит испытания и сертификацию в лаборатории (по согласованию с заказчиком);
- Поставка специализированных компонентов военного и аэрокосмического уровня качества (Xilinx, Altera, Analog Devices, Intersil, Interpoint, Microsemi, Actel, Aeroflex, Peregrine, VPT, Syfer, Eurofarad, Texas Instruments, MS Kennedy, Miteq, Cobham, E2V, MA-COM, Hittite, Mini-Circuits, General Dynamics и др.);

Компания «Океан Электроники» является официальным дистрибьютором и эксклюзивным представителем в России одного из крупнейших производителей разъемов военного и аэрокосмического назначения «JONHON», а так же официальным дистрибьютором и эксклюзивным представителем в России производителя высокотехнологичных и надежных решений для передачи СВЧ сигналов «FORSTAR».



## JONHON

«JONHON» (основан в 1970 г.)

Разъемы специального, военного и аэрокосмического назначения:

(Применяются в военной, авиационной, аэрокосмической, морской, железнодорожной, горно- и нефтедобывающей отраслях промышленности)

«FORSTAR» (основан в 1998 г.)

ВЧ соединители, коаксиальные кабели,  
кабельные сборки и микроволновые компоненты:

(Применяются в телекоммуникациях гражданского и специального назначения, в средствах связи, РЛС, а так же военной, авиационной и аэрокосмической отраслях промышленности).



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